

REPORT DOCUMENTATION PAGE

Form Approved
OMB No. 0704-0188

Public reporting burden for this collection of information is estimated to average 1 hour per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggestions for reducing this burden to Washington Headquarters Services, Directorate for Information Operations and Reports, 1215 Jefferson Davis Highway, Suite 1204, Arlington, VA 22202-4302, and to the Office of Management and Budget, Paperwork Reduction Project (0704-0188), Washington, DC 20503

1. AGENCY USE ONLY (Leave Blank)

2. REPORT DATE
1/31/98

3. REPORT TYPE AND DATES COVERED
Final

4. TITLE AND SUBTITLE
Advanced Heterostructure Workshop

5. FUNDING NUMBERS

6. AUTHOR(S)
Professor Joy Laskar

7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES)
Georgia Institute of Technology
School of Electrical & Computer Engineering
777 Atlantic Drive
Atlanta, GA 30332

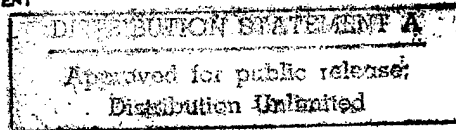
8. PERFORMING ORGANIZATION REPORT NUMBER
E21-812

9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES)
Office of Naval Research

10. SPONSORING/MONITORING AGENCY REPORT NUMBER

11. SUPPLEMENTARY NOTES COR:

12a. DISTRIBUTION/AVAILABILITY STATEMENT



12b. DISTRIBUTION CODE

13. ABSTRACT (Maximum 200 words)
The Advanced Heterostructure Workshop (AHW) follows in the tradition of the two conferences on Selectively Doped heterostructure Transistors (1984, 1986), three succeeding conferences on Advanced Heterostructure Transistors (1988, 1990, 1992) and the AHW in 1996. At the time of the first workshop, the HEMT was an emerging heterostructure transistor that had been made possible by breakthroughs in materials and sharp heterointerfaces. In the intervening years many related heterostructure devices have been developed, and the HEMT has been commercially employed as discrete transistors and in integrated circuits. This workshop will maintain the earlier tradition by placing a great emphasis on materials and physics for quantum devices. As usual, we will also cover some of the heterostructure technologies that are currently emerging into mainstream electronic and optoelectronic application areas. In addition, the AHW 1998 is soliciting contributions on recent advances and issues related to "Current Status and Future Prospects of III-V Industry for Electronics and Optoelectronics," "Wide Band-gap Electronics," and "Mesoscopic Electronics and Physics."

14. SUBJECT TERMS

15. NUMBER OF PAGES

16. PRICE CODE

17. SECURITY CLASSIFICATION OF REPORT

18. SECURITY CLASSIFICATION OF THIS PAGE

19. SECURITY CLASSIFICATION OF ABSTRACT

20. LIMITATION OF ABSTRACT

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Workshop Structure

The AHW has a virtually identical meeting structure to the Gordon Conferences which is considered by many to be one of the most productive of all meeting formats. It is a 4 1/2 day meeting with morning and evening sessions and with afternoons free for discussion among participants. The format of the meeting involves several overview presentations and a majority of short, 5 minute presentations of data that can be used as a framework for lively discussions. Each participant is expected to participate in these discussions and are encouraged to bring one or two extra overhead transparencies showing recent data that can be incorporated into the discussions. In the short presentations of data; titles, historical background and summaries are highly discouraged. No poster sessions are planned; everyone will have an opportunity to present their work in the discussion sessions and receive instant feedback. The AHW provides prominent device researchers the opportunity to exchange ideas in a focused format. A summary of the AHW will be published and made available to the attendees and general community.